

Silicon Diffused Power Transistor

BU4522AF

GENERAL DESCRIPTION

New generation, high-voltage, high-speed switching npn transistor in a plastic full-pack envelope intended for use in horizontal deflection circuits of colour TV receivers and PC monitors.

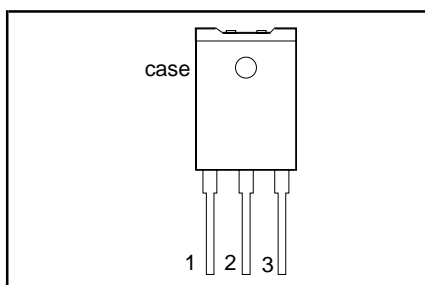
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0\text{ V}$	-	1500	V
V_{CEO}	Collector-emitter voltage (open base)		-	800	V
I_C	Collector current (DC)		-	10	A
I_{CM}	Collector current peak value		-	25	A
P_{tot}	Total power dissipation	$T_{hs} \leq 25\text{ °C}$	-	45	W
V_{CESat}	Collector-emitter saturation voltage	$I_C = 7\text{ A}; I_B = 1.75\text{ A}$	-	3.0	V
I_{Csat}	Collector saturation current (Fig 17)	$f = 16\text{ kHz}$	7	-	A
		$f = 64\text{ kHz}$	6	-	A
t_f	Fall time	$I_{Csat} = 7\text{ A}; f = 16\text{ kHz}$	285	400	ns
		$I_{Csat} = 6\text{ A}; f = 64\text{ kHz}$	170	230	ns

PINNING - SOT199

PIN	DESCRIPTION
1	base
2	collector
3	emitter
case	isolated

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	$V_{BE} = 0\text{ V}$	-	1500	V
V_{CEO}	Collector-emitter voltage (open base)		-	800	V
I_C	Collector current (DC)		-	10	A
I_{CM}	Collector current peak value		-	25	A
I_B	Base current (DC)		-	6	A
I_{BM}	Base current peak value		-	9	A
$-I_{BM}$	Reverse base current peak value ¹		-	6	A
P_{tot}	Total power dissipation	$T_{hs} \leq 25\text{ °C}$	-	45	W
T_{stg}	Storage temperature		-55	150	°C
T_j	Junction temperature		-	150	°C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j-hs}$	Junction to heatsink	with heatsink compound	-	2.8	K/W
$R_{th\ j-a}$	Junction to ambient	in free air	35	-	K/W

¹ Turn-off current.

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ISOLATION LIMITING VALUE & CHARACTERISTIC $T_{hs} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{isol}	Repetitive peak voltage from all three terminals to external heatsink	R.H. $\leq 65\%$; clean and dustfree	-	-	2500	V
C_{isol}	Capacitance from T2 to external heatsink	$f = 1\text{ MHz}$	-	22	-	pF

STATIC CHARACTERISTICS $T_{hs} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CES}	Collector cut-off current ²	$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$	-	-	1.0	mA
I_{CES}		$V_{BE} = 0\text{ V}; V_{CE} = V_{CESMmax}$ $T_j = 125\text{ }^{\circ}\text{C}$	-	-	2.0	mA
I_{EBO}	Emitter cut-off current	$V_{EB} = 7.5\text{ V}; I_C = 0\text{ A}$	-	-	1.0	mA
BV_{EBO}	Emitter-base breakdown voltage	$I_B = 1\text{ mA}$	7.5	13.5	-	V
$V_{CEOsust}$	Collector-emitter sustaining voltage	$I_B = 0\text{ A}; I_C = 100\text{ mA};$ $L = 25\text{ mH}$	800	-	-	V
V_{CEsat}	Collector-emitter saturation voltage	$I_C = 7\text{ A}; I_B = 1.75\text{ A}$	-	-	3.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C = 7\text{ A}; I_B = 1.75\text{ A}$	0.85	0.94	1.03	V
h_{FE}	DC current gain	$I_C = 1\text{ A}; V_{CE} = 5\text{ V}$	-	10	-	
h_{FE}		$I_C = 7\text{ A}; V_{CE} = 5\text{ V}$	4.2	5.8	7.3	

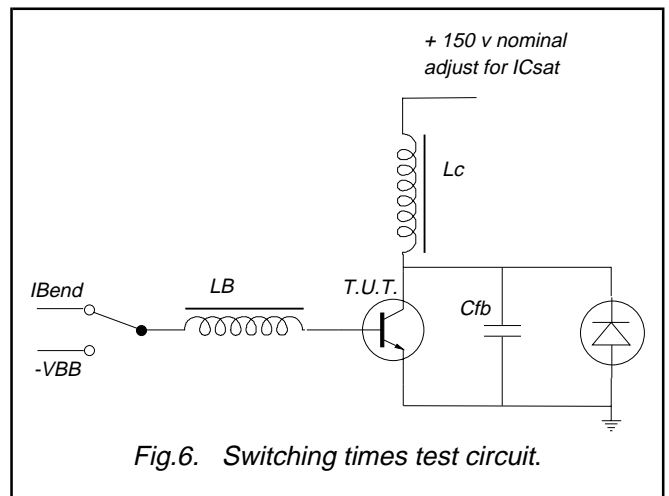
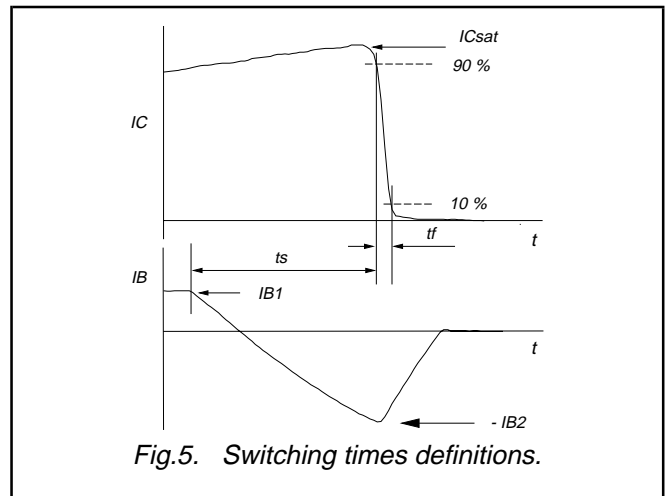
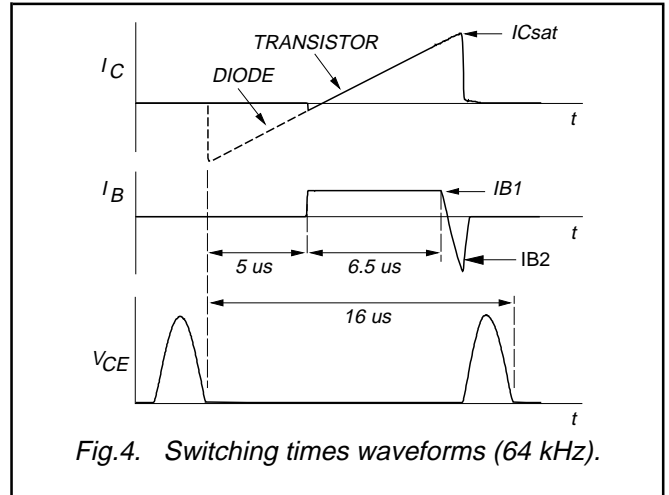
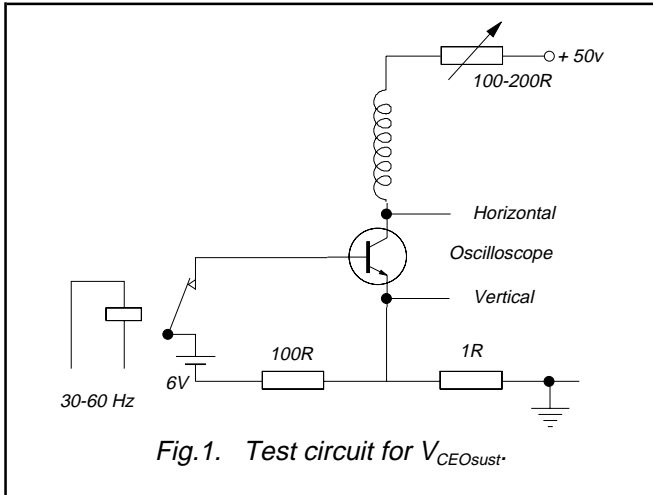
DYNAMIC CHARACTERISTICS $T_{hs} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
t_s	Switching times (16 kHz line deflection circuit)	$f = 16\text{ kHz}; I_{Csat} = 7\text{ A}; I_{B1} = 1.4\text{ A};$ $(I_{B2} = -3.5\text{ A})$			
t_f	Turn-off storage time		3.5	4.3	μs
t_f	Turn-off fall time		285	400	ns
t_s	Switching times (64 kHz line deflection circuit)	$f = 64\text{ kHz}; I_{Csat} = 6\text{ A}; I_{B1} = 1.2\text{ A};$ $(I_{B2} = -3.6\text{ A})$			
t_s	Turn-off storage time		2.3	2.7	μs
t_f	Turn-off fall time		170	230	ns

² Measured with half sine-wave voltage (curve tracer).

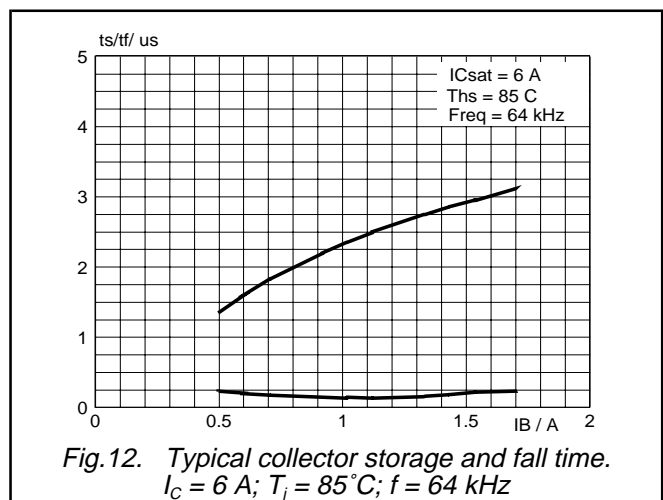
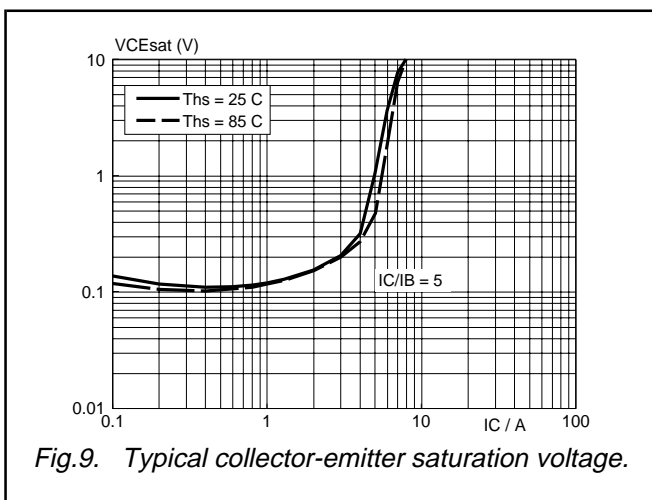
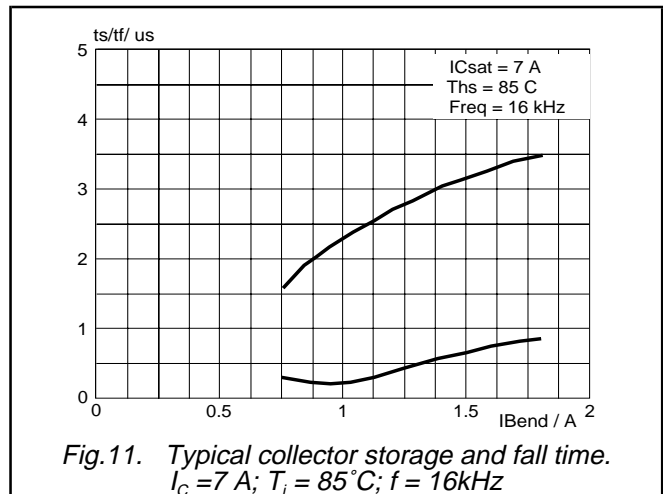
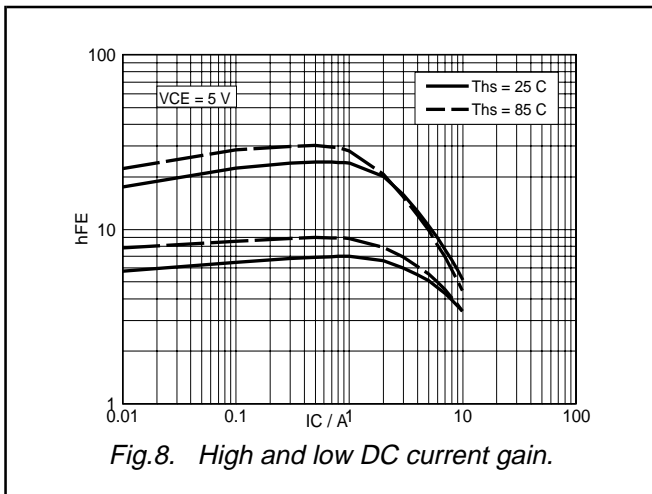
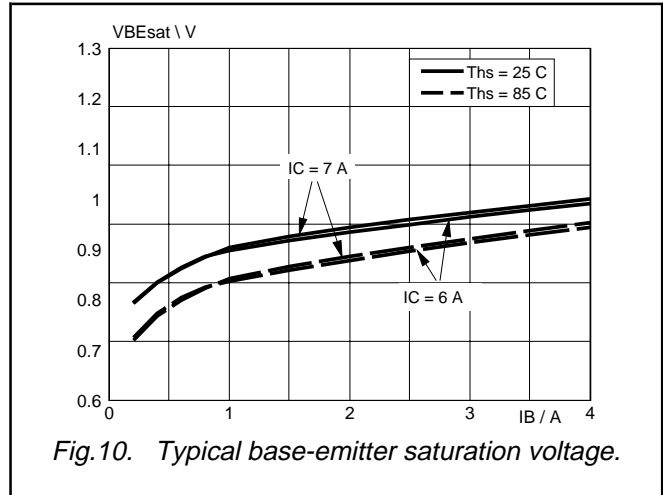
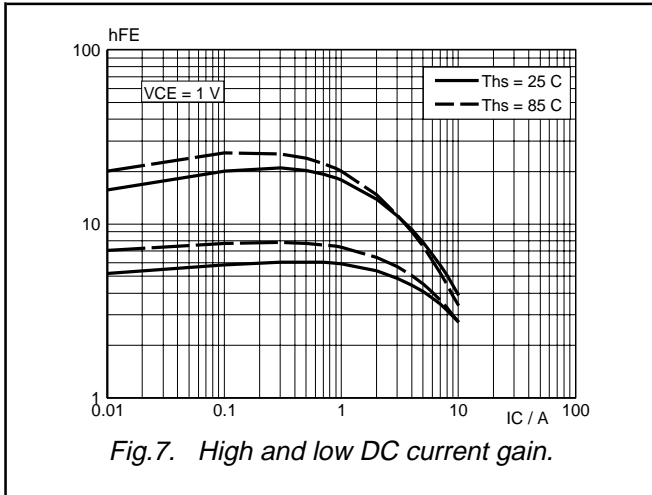
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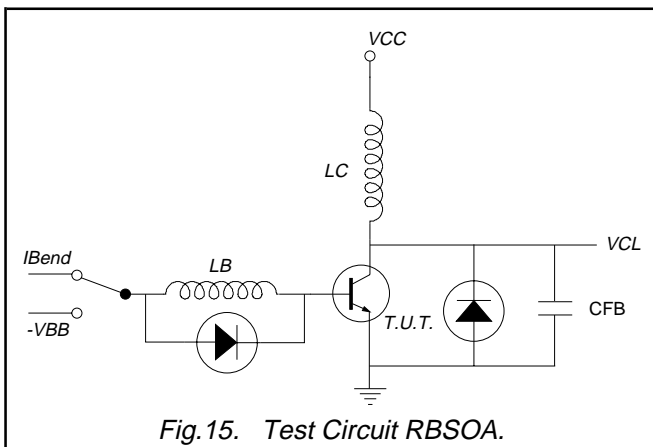
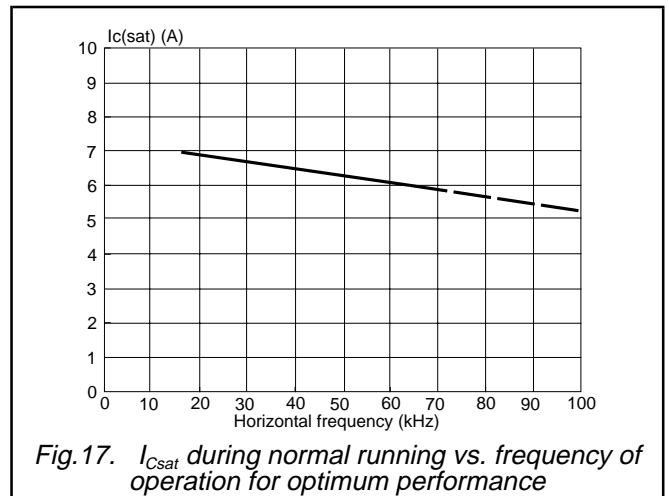
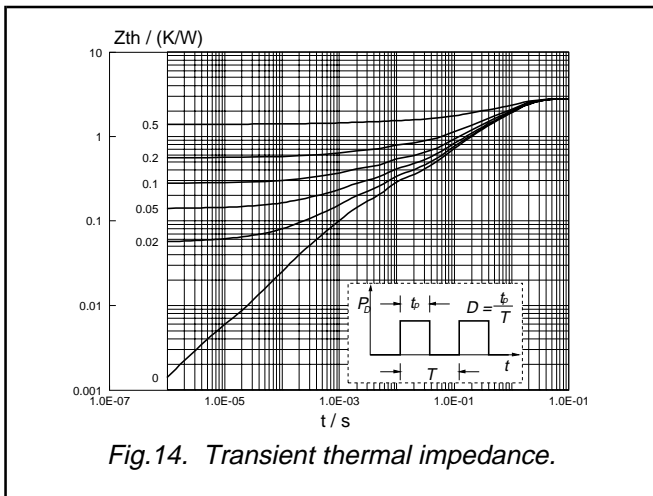
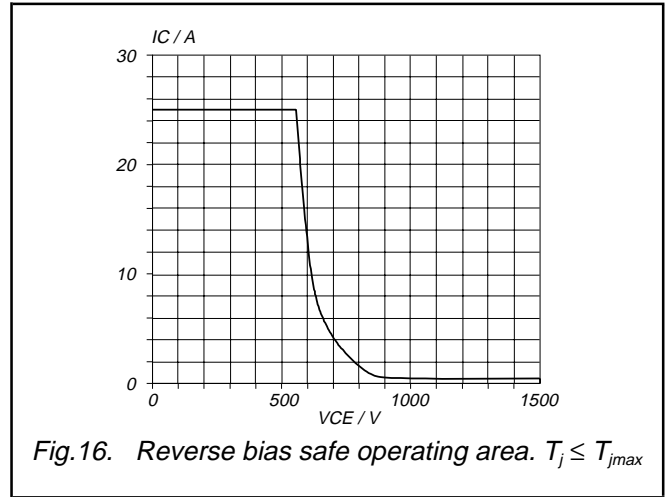
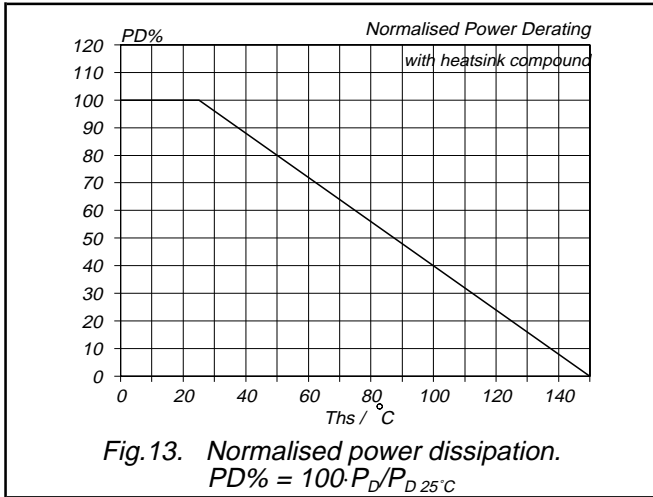
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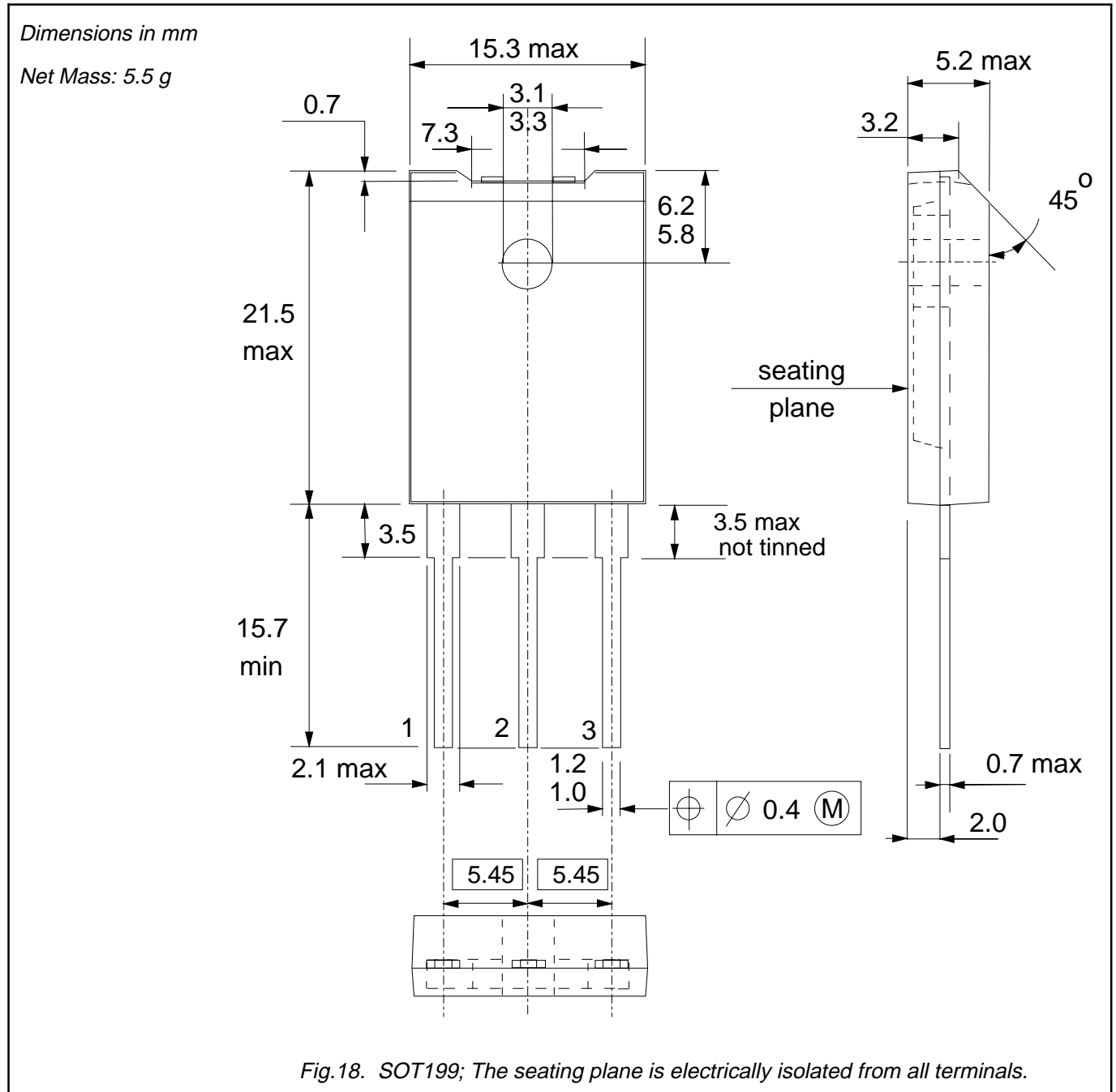
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MECHANICAL DATA



Notes

- 1. Refer to mounting instructions for F-pack envelopes.
- 2. Epoxy meets UL94 V0 at 1/8".